Elektronische Bauelemente

2SA1576A-C

-0.15A, -60V

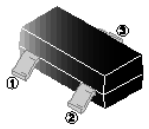
PNP Silicon Epitaxial Planer Transistors

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The 2SA1576A-C is designed for use in driver stage of AF amplifier and general purpose amplification.

SOT-323



FEATURES

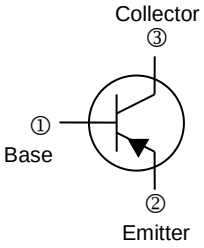
- Complements of the 2SC4081F-C
- Excellent h_{FE} Linearity

CLASSIFICATION OF h_{FE}

Product-Rank	2SA1576A-Q-C	2SA1576A-R-C	2SA1576A-S-C
Range	120~270	180~390	270~560
Marking	FQ	FR	FS

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-323	3K	7 inch



ORDER INFORMATION

Part Number	Type
2SA1576A-□-C	Lead (Pb)-free and Halogen-free

***□=h_{FE} Rank**

MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-150	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance from Junction-Ambient	$R_{\theta JA}$	625	°C/W
Junction & Storage Temperature Range	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60	-	-	V	I_C= -50μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-50	-	-	V	I_C= -1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-	-	V	I_E= -50μA, I_C=0
Collector Cut-off Current	I_{CBO}	-	-	0.1	μA	V_{CB}= -60V, I_E=0
Emitter Cut-off Current	I_{EBO}	-	-	0.1	μA	V_{EB}= -6V, I_C=0
DC Current Gain	h_{FE}	120	-	560		V_{CE}= -6V, I_C= -1mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-0.5	V	I_C= -50mA, I_B= -5mA
Transition Frequency	f_T	-	140	-	MHz	V_{CE}= -12V, I_C= -2mA, f=30MHz
Collector Output Capacitance	C_{ob}	-	4	5	pF	V_{CB}= -12V, I_E=0, f=1MHz

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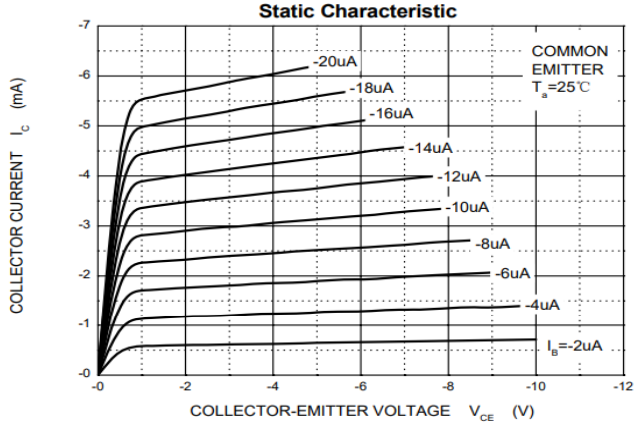
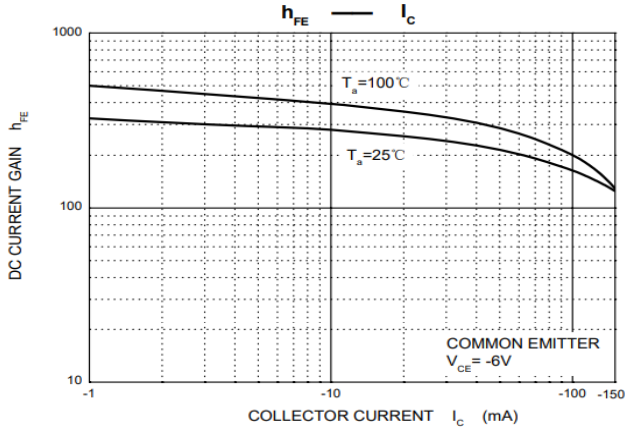
CHARACTERISTIC CURVES

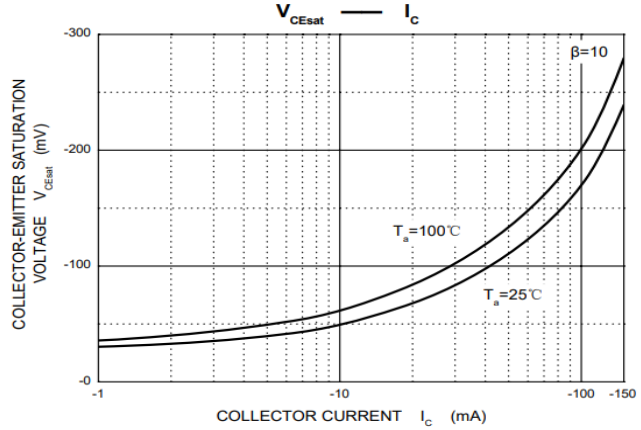
Static Characteristic



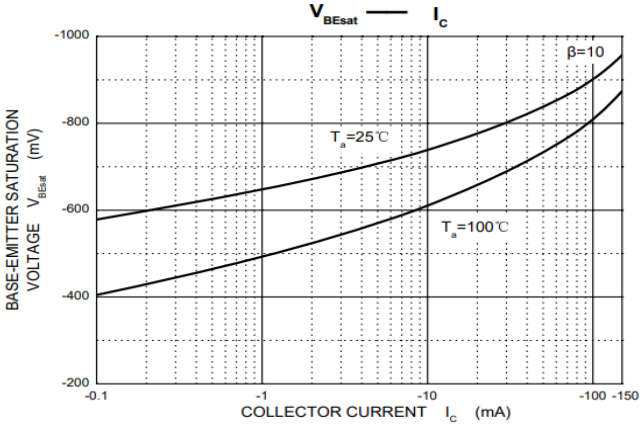
h_{FE} — I_C



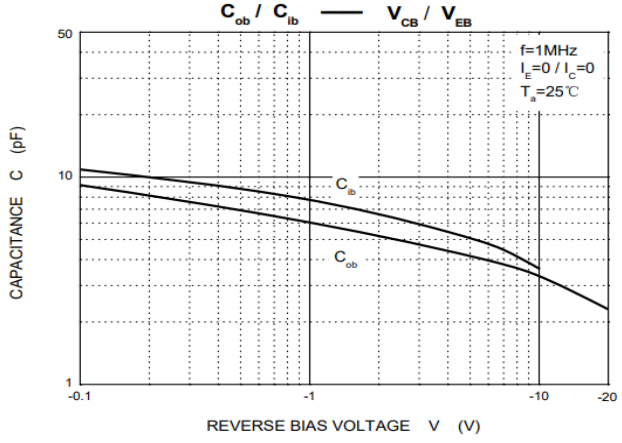
V_{CEsat} — I_C



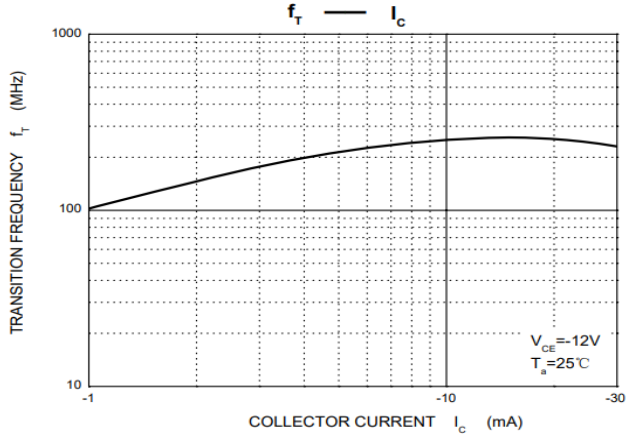
V_{BEsat} — I_C



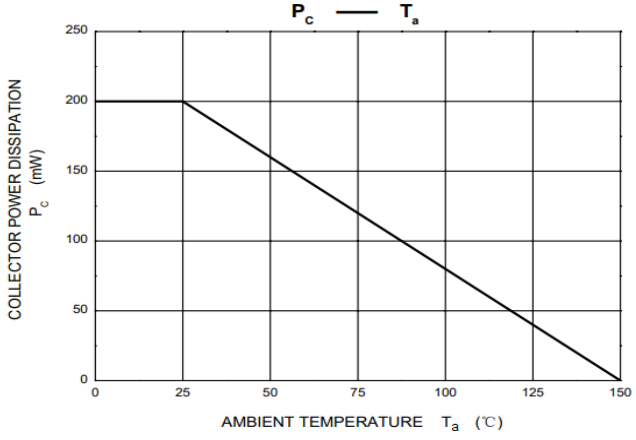
C_{ob} / C_{ib} — V_{CB} / V_{EB}



f_T — I_C



P_C — T_a



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PACKAGE OUTLINE DIMENSIONS

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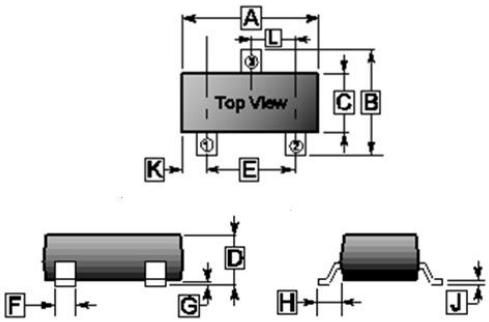
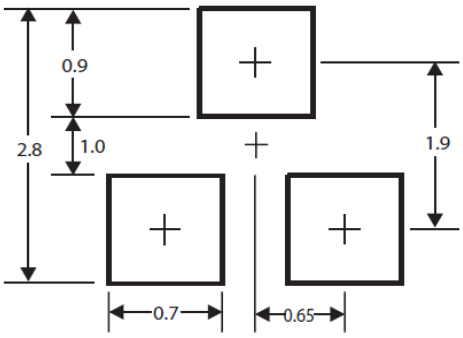


REF.	Millimeter	
	Min.	Max.
A	1.80	2.20
B	1.80	2.55
C	1.10	1.40
D	0.80	1.15
E	1.20	2.00
F	0.15	0.50
G	0.10 REF.	
H	0.525 REF.	
J	0.05	0.25
K	0.35 REF.	
L	0.65 TYP.	

MOUNTING PAD LAYOUT

SOT-323



*Dimensions in millimeters